

L Number	Hits	Search Text	DB	Time stamp
1	370	soi near10 (single near2 crystal\$6) near2 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 11:47
2	2400	low near2 temperature near10 (si or silicon) near2 deposit\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 11:48
3	2	("700") near5 low near2 temperature near10 (si or silicon) near2 deposit\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 11:48
4	70	low near2 temperature near10 (si or silicon) near2 single near2 crystal\$6 near2 deposit\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 11:49
27	5	pattern\$5 near10 (implant\$5) near10 (carbon or germanium) near10 (si or silicon) near2 (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 13:31
28	2	5953600.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 13:32
29	65519	bipolar near2 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 13:37
30	283	(bipolar near2 transistor) same (si silicon) near2 (single near2 crystal\$6) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 13:37
31	51	((bipolar near2 transistor) same (si silicon) near2 (single near2 crystal\$6) near2 substrate) same implant\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 13:33
32	18	((bipolar near2 transistor) same (si silicon) near2 (single near2 crystal\$6) near2 substrate) same implant\$6 same (pattern\$5 or mask\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 13:33
33	32	(bipolar near2 transistor) near5 emitter same (si silicon) near2 (single near2 crystal\$6) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 14:42
34	16	(mask\$5 or pattern\$5) near10 (getter\$5) near10 (si or silicon) near4 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 14:45
35	112	(mask\$5 or pattern\$5) near10 (getter\$5) near10 (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 15:12
36	31	implant\$5 near5 depth near5 less same (si or silicon) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 15:18

37	0	getter\$5 near5 depth near5 less same (si or silicon) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 15:18
38	0	getter\$5 near5 depth near5 nm same (si or silicon) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 15:19
39	37	implant\$5 near5 depth near5 nm same (si or silicon) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 15:19
-	2	6165265.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 13:49
-	26860	ion near4 implant\$4 same (silicon or si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 13:50
-	335	ion near4 implant\$4 same (silicon or si) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 13:51
-	6	ion near4 implant\$4 same (fl or flourine or fluorine) same (silicon or si) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 13:55
-	246	ion near4 implant\$4 same (fl or flourine or fluorine) and (silicon or si) near2 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 13:56
-	7	ion near4 implant\$4 same (fl or flourine or fluorine) and (silicon or si) near2 layer and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:07
-	62	ion near4 implant\$4 same (defect or damage) and (silicon or si) near2 layer and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:10
-	28	ion near4 implant\$4 same (defect or damage) same (silicon or si) near2 layer and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:19
-	17687	low near2 temperature same (silicon or si) near15 (epitax\$3) same (CVD or vapor near2 deposit\$4) 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:21
-	49	low near2 temperature same (silicon or si) near15 (epitax\$3) same (CVD or vapor near2 deposit\$4) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:21
-	14	low near2 temperature same (silicon or si) near15 (epitax\$3) same (CVD or vapor near2 deposit\$4) same (reduc\$3 or hydrogen or "h.sub.2" or h2) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 15:06

-	1	0386574.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/08 16:03
-	1	386574.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/08 16:23
-	3017	low near3 temperature near10 (si or silicon) near4 (deposit\$5 or growth)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/08 16:25
-	163	low near3 temperature near10 (si or silicon) near4 (deposit\$5 or growth) near10 (monocrystal\$4 or monocrystallin\$5 or single near4 crystal\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/08 16:26
-	36	(low near3 temperature near10 (si or silicon) near4 (deposit\$5 or growth) near10 (monocrystal\$4 or monocrystallin\$5 or single near4 crystal\$)) and 117\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/08 16:26
-	12	"933801"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/23 16:29
-	1266	implant\$5 near3 (neutral or atom) same (si or silicon) near5 (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 09:15
-	142	implant\$5 near3 (neutral or atom) same (si or silicon) near5 (substrate or wafer) same epitax\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 09:16
-	8	implant\$5 near3 (neutral) same (si or silicon) near5 (substrate or wafer) same epitax\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 09:19
-	9	implant\$5 near3 (fluorine or fl) same (si or silicon) near5 (substrate or wafer) same epitax\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 09:24
-	70	implant\$5 near3 (neutr\$5) same (si or silicon) near5 (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 10:06
-	2	implant\$5 near3 (neutr\$5) near10 (fluorine)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 10:07
-	5	implant\$5 near3 (neutr\$5) same (fluorine)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 10:09
-	127	electric\$6 near5 (neutr\$5) same (fluorine)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 11:32

-	1	electric\$6 near5 (neutr\$5) same (fluorine) same (si or silicon) near5 (wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 10:11
-	45	(neutr\$5) same (fluorine) same (si or silicon) near5 (wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 10:11
-	19	(neutr\$5) near10 (fluorine) same (si or silicon) near5 (wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 10:11
-	101	electric\$5 near5 neutral near10 (implant\$5 or embed\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 10:22
-	15	electric\$6 near5 (neutr\$5) near10 (fluorine)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 11:34
-	512	(neutr\$5) near10 (fluorine)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 11:34
-	3	(neutr\$5) near10 (fluorine) near10 implant\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 14:42
-	3	"6338507"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 14:43
-	2	"63038507"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 14:42
-	3	"06338507"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 16:27
-	26	(silicon or si) near10 epitax\$5 near5 (substrate or wafer) same (anneal\$5 or heat near2 treat\$5) near10 after near10 (deposit\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 16:52
-	2	5734195.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 16:55
-	468	czochralski near10 silicon near10 single near2 crystal\$5 near10 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 16:55
-	92	(czochralski near10 silicon near10 single near2 crystal\$5 near10 wafer) and @py<1997	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 16:56

-	16	((czochralski near10 silicon near10 single near2 crystal\$5 near10 wafer) and @py<1997) and 117/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 09:25
-	5	czochralski.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 16:57
-	3673	single near2 layer near5 (si or silicon) same (silicon or si) near5 (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 09:25
-	4512	single near2 crystal\$5 near2 layer near5 (si or silicon) same (silicon or si) near5 (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 09:26
-	3513	single near2 crystal\$5 near2 layer near5 (si or silicon) same (silicon or si) near5 (substrate or wafer) near5 single near2 crystal\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 09:26
-	560	single near2 crystal\$5 near2 layer near5 (si or silicon) same (silicon or si) near5 (substrate or wafer) near5 single near2 crystal\$ same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 09:27
-	425	single near2 crystal\$5 near2 layer near5 (si or silicon) near10 (silicon or si) near5 (substrate or wafer) near5 single near2 crystal\$ same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 09:27
-	97	single near2 crystal\$5 near2 layer near5 (si or silicon) near10 (silicon or si) near5 (substrate or wafer) near5 single near2 crystal\$ same temperature same (implant\$5 or defects)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 10:10
-	722	single near2 crystal\$5 near4 (si or silicon) near5 (substrate or wafer) same CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 10:12
-	25	(single near2 crystal\$5 near4 (si or silicon) near5 (substrate or wafer) same CMOS) and @py=1996	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 10:12
-	25	n\$1type near5 single near2 crystal\$5 near4 (si or silicon) near5 (substrate or wafer) same CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 10:22
-	27809	bipolar near2 transistor same emitter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 10:22
-	2481	(bipolar near2 transistor same emitter) and (si or silicon) near5 (substrate or wafer) same implant\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 10:23
-	1019	(bipolar near2 transistor same emitter) and (si or silicon) near5 (substrate or wafer) same implant\$5 same epitax\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 10:23

-	192	(bipolar near2 transistor same emitter) and (si or silicon) near5 (substrate or wafer) same implant\$5 same epitax\$5 same oxide near2 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 10:23
-	119	(bipolar near2 transistor same emitter) and (si or silicon) near5 (substrate or wafer) same implant\$5 same epitax\$5 near5 (si or silicon) same oxide near2 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 10:23
-	25	(bipolar near2 transistor same emitter) and (si or silicon) near5 (substrate or wafer) same implant\$5 same epitax\$5 near5 (si or silicon) same oxide near2 layer same anneal\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 11:08
-	95	(bipolar near2 transistor same emitter) and (si or silicon) near5 (substrate or wafer) same implant\$5 near10 oxide same anneal\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 11:13
-	1296	(si or silicon) near5 (substrate or wafer) same (boron or arsenic or phosphorous) near10 implant\$5 near10 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 11:14
-	20	(si or silicon) near5 (substrate or wafer) same (boron or arsenic or phosphorous) near10 implant\$5 near10 oxide same epitax\$5 near6 (silicon or si) same (heat near2 treat\$5 or anneal\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 11:22
-	1296	(si or silicon) near5 (substrate or wafer) same (boron or arsenic or phosphorous) near10 implant\$5 near10 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 11:25
-	306	(si or silicon) near5 (substrate or wafer) same (boron or arsenic or phosphorous) near10 implant\$5 near10 oxide same (anneal\$5 or heat near2 treat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 11:25
-	32	(si or silicon) near5 (substrate or wafer) same (boron or arsenic or phosphorous) near10 implant\$5 near10 oxide same (anneal\$5 or heat near2 treat\$5) near5 after	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 11:30
-	0	(si or silicon) near5 (substrate or wafer) same (boron or arsenic or phosphorous) near10 implant\$5 near10 oxide near10 (anneal\$5 or heat near2 treat\$5) near5 after near10 (deposit\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 11:36
-	10	(si or silicon) near5 (substrate or wafer) same (boron or arsenic or phosphorous) near10 implant\$5 near10 (anneal\$5 or heat near2 treat\$5) near5 after near10 (deposit\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 14:18
-	143	implant\$5 near10 getter\$5 same (anneal\$5 or heat near2 treat\$5) same (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 16:47
-	104	(implant\$5 near10 getter\$5 same (anneal\$5 or heat near2 treat\$5) same (si or silicon)) and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 16:47
-	20	implant\$5 near10 getter\$5 same (anneal\$5 or heat near2 treat\$5) same (si or silicon) same epitax\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 16:50

-	2712	implant\$5 same (anneal\$5 or heat near2 treat\$5) same (si or silicon) same epitax\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 16:50
-	1378	implant\$5 same (anneal\$5 or heat near2 treat\$5) same (si or silicon) near5 epitax\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 16:50
-	167	implant\$5 same (anneal\$5 or heat near2 treat\$5) near5 after same (si or silicon) near5 epitax\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 16:53
-	472	implant\$5 near5 (si or ge) same (si or silicon) near5 epitax\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 16:54
-	175	implant\$5 near5 (si or ge) same (si or silicon) near5 epitax\$6 same (anneal\$5 or heat near2 treat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 10:38
-	6	implant\$5 near5 (si or ge) same (si or silicon) near5 hetero\$1epitax\$6 same (anneal\$5 or heat near2 treat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 17:02
-	17	implant\$5 near5 (si or ge) same (si or silicon) near5 hetero\$1epitax\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 17:03
-	36	(si or silicon) near5 (single near5 crystal\$6) near10 (orientat\$5 near5 different)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/02 17:05
-	2074	implant\$5 near10 (si or silicon) near5 (substrate or wafer or layer) same (si or silicon) near5 epitax\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 10:22
-	1406	implant\$5 near5 (si or silicon) near5 (substrate or wafer or layer) same (si or silicon) near5 epitax\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 10:22
-	1046	implant\$5 near5 (si or silicon) near5 (substrate or wafer or layer) same (si or silicon) near5 epitax\$6 not same (anneal\$5 or heat near2 treat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 10:25
-	570	(implant\$5 near5 (si or silicon) near5 (substrate or wafer or layer) same (si or silicon) near5 epitax\$6 not same (anneal\$5 or heat near2 treat\$4)) and @py<2001	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 10:25
-	6	implant\$5 near5 (si or silicon) near5 (substrate or wafer or layer) same (si or silicon) near5 epitax\$6 same (anneal\$5 or heat near2 treat\$4) near5 without	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 10:23
-	576	implant\$5 near5 (si or silicon) near5 (substrate or wafer or layer) same (grow\$4 or deposit\$5) near5 (si or silicon) near5 epitax\$6 not same (anneal\$5 or heat near2 treat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 10:26

-	22	implant\$5 near5 (si or ge) same (si or silicon) near5 epitax\$6 same (anneal\$5 or heat near2 treat\$5) near5 after	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 10:45
-	34	implant\$5 near5 (si or silicon) near5 (substrate or wafer or layer) near5 amorphous near10 epitax\$6 same (anneal\$5 or heat near2 treat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 10:57
-	266	implant\$5 near5 (si or silicon) near5 (substrate or wafer or layer) near10 epitax\$6 same (anneal\$5 or heat near2 treat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:01
-	138	implant\$5 near5 (si or silicon) near5 (substrate or wafer or layer) near10 epitax\$6 near10 (anneal\$5 or heat near2 treat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:10
-	282	single near2 crystal\$5 near5 (si or silicon) near10 (amorphous near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:14
-	60	(grow\$4 or deposit\$5) near4 single near2 crystal\$5 near5 (si or silicon) near10 (amorphous near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:15
-	2	"9064016"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:56
-	2	"09064016"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:36
-	122	low near2 dose near10 implant\$5 same (si or silicon) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:37
-	49	low near2 dose near10 implant\$5 near10 (si or silicon) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:37
-	0	low near2 dose near10 implant\$5 near10 (si or silicon) near2 substrate same epitax\$5 near2 (deposit\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:37
-	0	low near2 dose near10 implant\$5 near10 (si or silicon) near2 substrate same epitax\$5 near10 (deposit\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:38
-	2	low near2 dose near10 implant\$5 near10 (si or silicon) near2 substrate same epitax\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 14:07
-	972	oxide near2 layer near10 implant\$5 near10 (si or silicon) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 14:09



-	5	oxide near2 layer near10 implant\$5 near5 carbon near10 (si or silicon) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 14:08
-	11	oxide near2 layer near10 low near5 implant\$5 near10 (si or silicon) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 14:09
-	1939	implant\$5 near10 through near5 (oxide or "sio.sub.2") same (si or silicon) near5 (substrate or layer or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 14:14
-	15	(carbon or germanium) near10 implant\$5 near10 through near5 (oxide or "sio.sub.2") same (si or silicon) near5 (substrate or layer or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 15:36
-	6	(carbon ) near10 implant\$5 near10 through near5 (oxide or "sio.sub.2") same (si or silicon) near5 (substrate or layer or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 14:15
-	0	silicon near2 on near2 insulator near10 (single near2 crystal\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 15:36
-	1209	silicon near2 insulator near10 (single near2 crystal\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 15:36
-	219	silicon near2 insulator near10 (single near2 crystal\$6) near2 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 15:37
-	205	silicon near2 insulator near10 (single near2 crystal\$6) near2 wafer near2 (si silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 15:37
-	41	silicon near2 insulator near10 (single near2 crystal\$6) near2 wafer near2 (si silicon) and @py<1998	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/05 11:26
-	2	5024723.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 15:43